RENESAS

RJK2057DPA

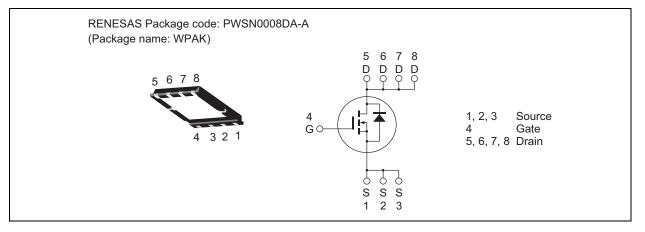
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1761-0200 Rev.2.00 Jan 14, 2009

Features

- Low on-resistance
- Low drive current ٠
- High density mounting

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID	20	А
Drain peak current	Note1 I _{D (pulse)}	40	А
Body-drain diode reverse drain current	I _{DR}	20	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	40	А
Avalanche current	I _{AP} ^{Note3}	9	А
Avalanche energy	E _{AR} ^{Note3}	5.4	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	٥°

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at $Tc = 25^{\circ}C$

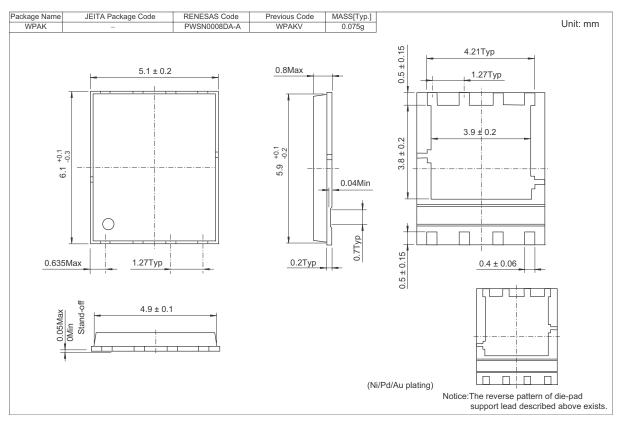
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—		1	μΑ	$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	—		±1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	—	0.068	0.085	Ω	$I_D = 10 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1250	_	pF	V _{DS} = 25 V
Output capacitance	Coss	—	245	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	—	25	_	pF	
Turn-on delay time	t _{d(on)}	—	23	—	ns	$I_D = 10 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 10 \Omega$ $Rg = 10 \Omega$
Rise time	tr	—	46	—	ns	
Turn-off delay time	t _{d(off)}	—	35	—	ns	
Fall time	t _f	—	28	—	ns	
Total gate charge	Qg	—	19	—	nC	$V_{DD} = 160 V$ $V_{GS} = 10 V$ $I_D = 20 A$
Gate to source charge	Qgs	—	6.9	—	nC	
Gate to drain charge	Qgd	_	5.3		nC	
Body-drain diode forward voltage	V _{DF}	—	0.90	1.35	V	$I_F = 20 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	—	145	_	ns	I _F = 20 A, V _{GS} = 0 di _F /dt = 100 A/μs

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2057DPA-00-J0	2500 pcs	Taping

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

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